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Vishay Semiconductors

# Medium Power Phase Control Thyristors (Stud Version), 50 A



PRIMARY CHARACTERISTICS				
I <sub>T(AV)</sub>	50 A			
$V_{DRM}/V_{RRM}$	100 V, 200 V, 400 V, 600 V, 800 V, 1000 V, 1200 V			
$V_{TM}$	1.60 V			
I <sub>GT</sub>	100 mA			
T <sub>J</sub>	-40 °C to 125 °C			
Package	TO-65 (TO-208AC)			
Circuit configuration	Single SCR			

#### **FEATURES**

- High current rating
- Excellent dynamic characteristics
- dV/dt = 1000 V/µs option
- · Superior surge capabilities
- Standard package
- · Metric threads version available
- Types up to 1200 V V<sub>DRM</sub>/V<sub>RRM</sub>
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### **TYPICAL APPLICATIONS**

- · Phase control applications in converters
- · Lighting circuits
- Battery charges
- Regulated power supplies and temperature and speed control circuit

PARAMETER	TEST CONDITIONS	VALUES	UNITS	
1		50	A	
I <sub>T(AV)</sub>	T <sub>C</sub>	94	°C	
I <sub>T(RMS)</sub>		80	A	
I <sub>TSM</sub>	50 Hz	1430	Α	
	60 Hz	1490		
<sup>2</sup> t	50 Hz	10.18	kA <sup>2</sup> s	
1-1	60 Hz	9.30	- KA2S	
V <sub>DRM</sub> /V <sub>RRM</sub>		100 to 1200	V	
t <sub>q</sub>	Typical	110	μs	
TJ		-40 to +125	°C	

#### **ELECTRICAL SPECIFICATIONS**

VOLTAGE RATINGS							
TYPE NUMBER	VOLTAGE CODE	V <sub>DRM</sub> /V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE <sup>(1)</sup> V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK VOLTAGE <sup>(2)</sup> V	$ \begin{vmatrix} I_{DRM}/I_{RRM} & MAXIMUM & AT \\ T_J = T_J & MAXIMUM \\ & mA \end{vmatrix} $			
	10	100	150				
	20	200	300				
	40	400	500				
VS-50RIA	60	600	700	15			
	80	800	900				
	100	1000	1100				
	120	1200	1300				

#### Notes

 $<sup>^{(1)}</sup>$  Units may be broken over non-repetitively in the off-state direction without damage, if dl/dt does not exceed 20 A/ $\mu$ s

 $<sup>\</sup>ensuremath{^{(2)}}$  For voltage pulses with  $t_p \leq 5 \ ms$ 



ABSOLUTE MAXIMUM RATII	NGS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS	
Maximum average on-state current	1	180° sinusoidal conduction		50	Α	
at case temperature	I <sub>T(AV)</sub>	100 3110301	dai conduction		94	°C
Maximum RMS on-state current	I <sub>T(RMS)</sub>				80	Α
		t = 10 ms	No voltage		1430	
Maximum peak, one-cycle	l	t = 8.3 ms	reapplied		1490	Α
non-repetitive surge current	I <sub>TSM</sub>	t = 10 ms	100 % V <sub>RRM</sub>		1200	_ A
		t = 8.3 ms	reapplied	Sinusoidal half wave,	1255	
		t = 10 ms	No voltage	initial $T_J = T_J$ maximum	10.18	- kA <sup>2</sup> s
Maximum I <sup>2</sup> t for fusing	l <sup>2</sup> t	t = 8.3 ms	reapplied		9.30	
	1-1	t = 10 ms	100 % V <sub>RRM</sub>		7.20	
		t = 8.3 ms	reapplied		6.56	
Maximum $I^2 \sqrt{t}$ for fusing	I <sup>2</sup> √t	t = 0.1 to 10 ms, no voltage reapplied, $T_J = T_J$ maximum		101.8	kA²√s	
Low level value of threshold voltage	V <sub>T(TO)1</sub>	(16.7 % x $\pi$ x $I_{T(AV)}$ < I < $\pi$ x $I_{T(AV)}$ ), $T_J = T_J$ maximum		0.94	V	
High level value of threshold voltage	V <sub>T(TO)2</sub>	$(\pi \times I_{T(AV)} < I$	< 20 x π x I <sub>T(AV)</sub> ),	T <sub>J</sub> = T <sub>J</sub> maximum	1.08	V
Low level value of on-state slope resistance	r <sub>t1</sub>	(16.7 % x $\pi$ x $I_{T(AV)}$ < I < $\pi$ x $I_{T(AV)}$ ), $T_J = T_J$ maximum		4.08	mΩ	
High level value of on-state slope resistance	r <sub>t2</sub>	$(\pi \times I_{T(AV)} < I < 20 \times \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$ 3.34		11122		
Maximum on-state voltage	$V_{TM}$	I <sub>pk</sub> = 157 A, T <sub>J</sub> = 25 °C		1.60	V	
Maximum holding current	I <sub>H</sub>	$T_J$ = 25 °C, anode supply 22 V, resistive load, initial $I_T$ = 2 A		200	mA	
Latching current	ΙL	Anode supp	ly 6 V, resistive lo	ad	400	

SWITCHING						
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum rate of	$V_{DRM} \le 600 \text{ V}$	dl/dt	$T_C$ = 125 °C, $V_{DM}$ = Rated $V_{DRM}$ , Gate pulse = 20 V, 15 Ω, $t_D$ = 6 μs, $t_T$ = 0.1 μs maximum	200	A/µs	
rise of turned-on current $V_{DRM} \le 1$	$V_{DRM} \le 1600 \text{ V}$		$I_{TM} = (2 \text{ x rated dl/dt}) \text{ A}$	100	<i>τ</i> νμ5	
Typical delay time		$t_{\rm d}$ $T_{\rm C}$ = 25 °C, $V_{\rm DM}$ = Rated $V_{\rm DRM}$ , $I_{\rm TM}$ = 10 A dc resistive circuit Gate pulse = 10 V, 15 $\Omega$ source, $t_{\rm p}$ = 20 $\mu$ s		0.9		
Typical turn-off time		t <sub>q</sub>	$t_{\rm q}$ $T_{\rm C}$ = 125 °C, $I_{\rm TM}$ = 50 A, reapplied dV/dt = 20 V/µs dIr/dt = - 10 A/µs, $V_{\rm R}$ = 50 V		μs	

BLOCKING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum critical rate of rise of	dV/dt	T <sub>J</sub> = T <sub>J</sub> maximum linear to 100 % rated V <sub>DRM</sub>	200	1//110	
off-state voltage	av/at	T <sub>J</sub> = T <sub>J</sub> maximum linear to 67 % rated V <sub>DRM</sub>	500 <sup>(1)</sup>	V/µs	

#### Note

 $<sup>^{(1)}</sup>$  Available with dV/dt = 1000 V/ $\mu s$ , to complete code add S90 i.e. 50RIA120S90



TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum peak gate power	P <sub>GM</sub>	$T_J = T_J$ maximum, $t_p \le \xi$	$T_J = T_J$ maximum, $t_p \le 5$ ms		w
Maximum average gate power	P <sub>G(AV)</sub>			2.5	] vv
Maximum peak positive gate current	I <sub>GM</sub>			2.5	А
Maximum peak positive gate voltage	+V <sub>GM</sub>			20	V
Maximum peak negative gate voltage	-V <sub>GM</sub>			10	\ \ \
	I <sub>GT</sub>	T <sub>J</sub> = - 40 °C	Maximum required gate trigger current/voltage are the lowest value which will trigger all units 6 V	250	mA
DC gate current required to trigger		T <sub>J</sub> = 25 °C		100	
		T <sub>J</sub> = 125 °C		50	
DC gate valtage required to this say	.,,	T <sub>J</sub> = - 40 °C	anode to cathode applied	3.5	V
DC gate voltage required to trigger	V <sub>GT</sub>	T <sub>J</sub> = 25 °C	2.5	V	
DC gate current not to trigger	I <sub>GD</sub>	T <sub>J</sub> = T <sub>J</sub> maximum, V <sub>DRM</sub> = Rated voltage	Maximum gate current/voltage not to trigger is the maximum	5.0	mA
DC gate voltage not to trigger	$V_{\mathrm{GD}}$	$T_J = T_J \text{ maximum}$	value which will not trigger any unit with rated V <sub>DRM</sub> anode to cathode applied	0.2	V

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-40 to +125	°C	
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	DC operation	0.35	K/W	
Maximum thermal resistance, case to heat sink	R <sub>thCS</sub>	Mounting surface, smooth, flat and greased	0.25	r./ VV	
Allowable requesting toward		Non-lubricated threads	3.4 + 0 - 10 % (30)	N · m	
Allowable mounting torque		Lubricated threads	2.3 + 0 - 10 % (20)	(lbf·in)	
Approximate weight			28	g	
Approximate weight			1.0	OZ.	
Case style		See dimensions - link at the end of datasheet	dimensions - link at the end of datasheet TO-65 (TO-20		

△R <sub>th</sub> JC CONDUCTION							
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS			
180°	0.078	0.057					
120°	0.094	0.098					
90°	0.120	0.130	$T_J = T_J \text{ maximum}$	K/W			
60°	0.176	0.183					
30°	0.294	0.296					

#### Note

The table above shows the increment of thermal resistance R<sub>thJC</sub> when devices operate at different conduction angles than DC

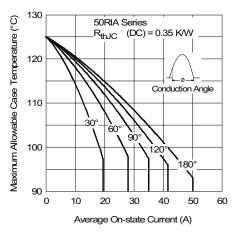


Fig. 1 - Current Ratings Characteristics

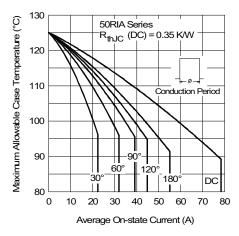


Fig. 2 - Current Ratings Characteristics

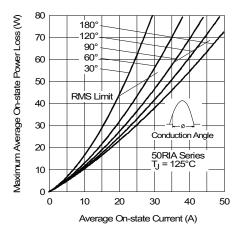


Fig. 3 - On-State Power Loss Characteristics

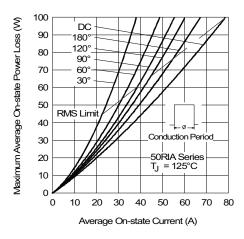


Fig. 4 - On-State Power Loss Characteristics

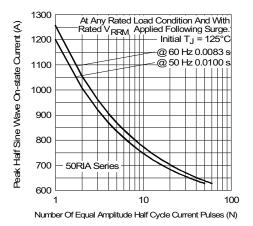


Fig. 5 - Maximum Non-Repetitive Surge Current

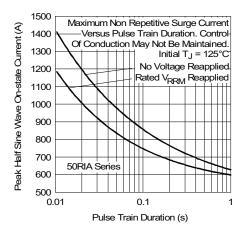


Fig. 6 - Maximum Non-Repetitive Surge Current

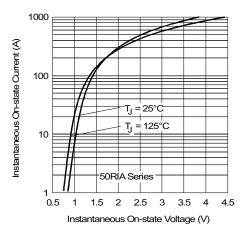


Fig. 7 - Forward Voltage Drop Characteristics

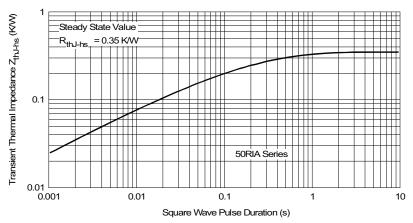


Fig. 8 - Thermal Impedance Z<sub>thJC</sub> Characteristics

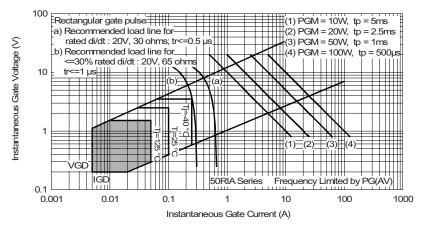
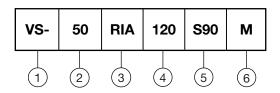


Fig. 9 - Gate Characteristics



#### **ORDERING INFORMATION TABLE**

#### Device code



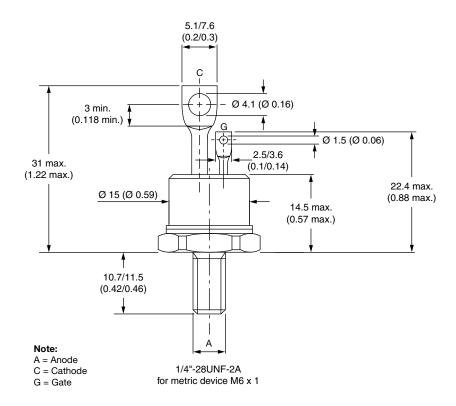
- 1 Vishay Semiconductors product
- 2 Current code
- Essential part number
- Voltage code x 10 = V<sub>RRM</sub> (see Voltage Ratings table)
- 5 Critical dV/dt:
  - None = 500 V/µs (standard value)
  - S90 = 1000 V/µs (special selection)
- 6 • None = stud base TO-65 (TO-208AC) 1/4" 28UNF-2A
  - M = stud base TO-65 (TO-208AC) M6 x 1

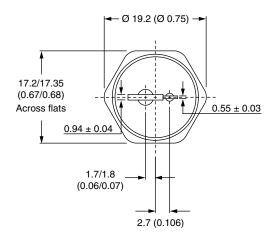
LINKS TO RELATED DOCUMENTS			
Dimensions	www.vishay.com/doc?95334		



# TO-208AC (TO-65)

### **DIMENSIONS** in millimeters (inches)







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T2160N28TOF VT TT251N16KOF-K VS-22RIA100 VS-16RIA40 TD250N16KOF-A VS-ST110S16P0 T930N36TOF VT T2160N24TOF

VT T1190N18TOF VT T1590N28TOF VT 2N1776A T590N14TOF NTE5375 NTE5460 NTE5481 NTE5512 NTE5514 NTE5518

NTE5519 NTE5529 NTE5553 NTE5555 NTE5557 NTE5567 NTE5570 NTE5570 NTE5574 NTE5576 NTE5579 NTE5589 NTE5592

NTE5598